NSN 5961-00-504-0210

Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-504-0210 **Inclosure Material:** Glass **Overall Length:** 0.213 inches **Overall Width:** 0.320 inches **Component Name And Quantity:** 2 semiconductor device diode **Mounting Method:** Press fit **Semiconductor Material:** Silicon all semiconductor device diode Voltage Rating In Volts Per Characteristic: 70.0 reverse voltage, peak all semiconductor device diode **Current Rating Per Characteristic:** 200.00 milliamperes forward current, average blank all semiconductor device diode and 500.00 milliamperes peak forward surge current nanoamperes all semiconductor device diode **Power Rating Per Characteristic:** 225.0 milliwatts small-signal input power, common-collector absolute all semiconductor device diode **Maximum Operating Tempurature Per Measurement Point:** 135.0 degrees celsius junction **Special Features:** Common anode; all semiconductor device diode junction pattern arrangement: pn **Terminal Type And Quantity:** 3 ribbon Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: A110a0